Marco Fanciulli

List of Publications by Year in descending order

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437	12,332	46918	42291
papers	citations	47 h-index	92 g-index

442	442	442	12145
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Large Spinâ€toâ€Charge Conversion at Room Temperature in Extended Epitaxial Sb₂Te₃ Topological Insulator Chemically Grown on Silicon. Advanced Functional Materials, 2022, 32, 2109361.	7.8	19
2	Superconducting micro-resonators for electron spin resonance - the good, the bad, and the future. Journal of Magnetic Resonance, 2022, 334, 107102.	1.2	7
3	Magnetic Transitions and Energy Transfer Processes in Sb-Based Zero-Dimensional Metal Halide Nanocrystals Doped with Manganese. ACS Energy Letters, 2022, 7, 1566-1573.	8.8	21
4	Optical and Magneto-Optical Properties of Donor-Bound Excitons in Vacancy-Engineered Colloidal Nanocrystals. Nano Letters, 2021, 21, 6211-6219.	4.5	2
5	Spinâ€Charge Conversion in Fe/Au/Sb₂Te₃ Heterostructures as Probed By Spin Pumping Ferromagnetic Resonance. Advanced Materials Interfaces, 2021, 8, 2101244.	1.9	11
6	Fe/Sb₂Te₃ Interface Reconstruction through Mild Thermal Annealing. Advanced Materials Interfaces, 2020, 7, 2000905.	1.9	5
7	Bright Blue Emitting Cu-Doped Cs₂ZnCl₄ Colloidal Nanocrystals. Chemistry of Materials, 2020, 32, 5897-5903.	3.2	63
8	ALD growth of ultra-thin Co layers on the topological insulator Sb2Te3. Nano Research, 2020, 13, 570-575.	5.8	10
9	Ferromagnetic resonance of Co thin films grown by atomic layer deposition on the Sb2Te3 topological insulator. Journal of Magnetism and Magnetic Materials, 2020, 509, 166885.	1.0	9
10	Probing two-level systems with electron spin inversion recovery of defects at the Si/SiO2 interface. Physical Review Research, 2020, 2, .	1.3	4
11	Phonon-induced relaxation and decoherence times of the hybrid qubit in silicon quantum dots. Physical Review B, 2019, 100, .	1.1	4
12	Spin-lattice relaxation processes of transition metal ions in a heavily cobalt doped ZnO: Phonon heating effect. Journal of Applied Physics, 2019, 126, 123903.	1.1	2
13	Towards Oxide Electronics: a Roadmap. Applied Surface Science, 2019, 482, 1-93.	3.1	236
14	Non-Ideal X-Gate and Z-Gate in Semiconducting Spin Qubit Implementations. Proceedings (mdpi), 2019, 12, .	0.2	0
15	Ambient atmosphere laser-induced local ripening of MoS₂ nanoparticles. Journal of Materials Chemistry C, 2019, 7, 13261-13266.	2.7	2
16	Trap-Mediated Two-Step Sensitization of Manganese Dopants in Perovskite Nanocrystals. ACS Energy Letters, 2019, 4, 85-93.	8.8	92
17	In-doped Sb nanowires grown by MOCVD for high speed phase change memories. Micro and Nano Engineering, 2019, 2, 117-121.	1.4	5
18	Chemical, structural and magnetic properties of the Fe/Sb2Te3 interface. Journal of Magnetism and Magnetic Materials, 2019, 474, 632-636.	1.0	13

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19	Engineering Domain-Wall Motion in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>Co</mml:mi><mml:mtext>â^'</mml:mtext><mml:mi>Fe</mml:mi><mml:mtext>â^'</mml:mtext><mml:mrow><mml:mi mathvariant="normal">B</mml:mi></mml:mrow><mml:mrow><mml:mo>/</mml:mo><mml:mi>Mg</mml:mi><mml:mi mathvariant="normal">O</mml:mi></mml:mrow></mml:math> Ultrathin Films with Perpendicular Anisotropy Using Patterned Substrates with Subnanometer Step Modulation. Physical Review Applied, 2018, 10, .	4.5	4
20	Gate fidelity comparison in semiconducting spin qubit implementations affected by control noises. Journal of Physics Communications, 2018, 2, 115022.	0.5	5
21	Coherence Time Analysis in Semiconducting Hybrid Qubit under Realistic Experimental Conditions. Advanced Quantum Technologies, 2018, 1, 1800040.	1.8	7
22	Colloidal Synthesis of Double Perovskite Cs₂AgInCl₆ and Mn-Doped Cs₂AgInCl₆ Nanocrystals. Journal of the American Chemical Society, 2018, 140, 12989-12995.	6.6	397
23	Semiconducting double-dot exchange-only qubit dynamics in the presence of magnetic and charge noises. Quantum Information Processing, 2018, 17, 1.	1.0	6
24	(Invited) Analog HfO2-RRAM Switches for Neural Networks. ECS Transactions, 2017, 75, 85-94.	0.3	15
25	Thermal resistance measurement of In₃SbTe₂ nanowires. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600500.	0.8	5
26	Controlled-NOT gate sequences for mixed spin qubit architectures in a noisy environment. Quantum Information Processing, 2017, 16, 1.	1.0	6
27	Atomic-scale study of the amorphous-to-crystalline phase transition mechanism in GeTe thin films. Scientific Reports, 2017, 7, 8234.	1.6	14
28	Analog Memristive Synapse in Spiking Networks Implementing Unsupervised Learning. Frontiers in Neuroscience, 2016, 10, 482.	1.4	142
29	MOCVD growth and structural characterization of Inâ€“Sbâ€“Te nanowires. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 335-338.	0.8	14
30	Electron Confinement at the Si/MoS₂ Heterosheet Interface. Advanced Materials Interfaces, 2016, 3, 1500619.	1.9	28
31	Strong confinement-induced engineering of the g factor and lifetime of conduction electron spins in Ge quantum wells. Nature Communications, 2016, 7, 13886.	5.8	28
32	HfO2-based memristors for neuromorphic applications. , 2016, , .		32
33	Experimental study of gradual/abrupt dynamics of HfO2-based memristive devices. Applied Physics Letters, 2016, 109, .	1.5	49
34	Hardness, elastic modulus, and wear resistance of hafnium oxide-based films grown by atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	0.9	32
35	(Invited) Silicon Nanowires: Donors, Surfaces and Interface Defects. ECS Transactions, 2016, 75, 179-187.	0.3	0
36	Low power phase change memory switching of ultra-thin In3Sb1Te2 nanowires. Applied Physics Letters, 2016, 109, .	1.5	18

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37	Atomic Layer Deposition of hexagonal ErFeO3 thin films on SiO2/Si. Thin Solid Films, 2016, 604, 18-22.	0.8	6
38	Maximum density of quantum information in a scalable CMOS implementation of the hybrid qubit architecture. Quantum Information Processing, 2016, 15, 2253-2274.	1.0	18
39	Modular Printed Circuit Boards for Broadband Characterization of Nanoelectronic Quantum Devices. IEEE Transactions on Instrumentation and Measurement, 2016, 65, 1827-1835.	2.4	11
40	Engineering organic/inorganic alumina-based films as dielectrics for red organic light emitting transistors. Thin Solid Films, 2016, 616, 408-414.	0.8	9
41	Engineering the Growth of MoS₂ via Atomic Layer Deposition of Molybdenum Oxide Film Precursor. Advanced Electronic Materials, 2016, 2, 1600330.	2.6	41
42	P-164: Organic Light Emitting Transistors (OLETs) using ALD-grown Al₂O₃dielectric. Digest of Technical Papers SID International Symposium, 2016, 47, 1737-1739.	0.1	3
43	A compact T-shaped nanodevice for charge sensing of a tunable double quantum dot in scalable silicon technology. Physics Letters, Section A: General, Atomic and Solid State Physics, 2016, 380, 1205-1209.	0.9	5
44	Protective coatings of hafnium dioxide by atomic layer deposition for microelectromechanical systems applications. Applied Surface Science, 2016, 368, 470-476.	3.1	11
45	Defects and Dopants in Silicon Nanowires Produced by Metal-Assisted Chemical Etching. ECS Journal of Solid State Science and Technology, 2016, 5, P3138-P3141.	0.9	5
46	Electroporation Enhances Bleomycin Efficacy in Cats with Periocular Carcinoma and Advanced Squamous Cell Carcinoma of the Head. Journal of Veterinary Internal Medicine, 2015, 29, 1368-1375.	0.6	35
47	Coherent tunneling by adiabatic passage of an exchange-only spin qubit in a double quantum dot chain. Physical Review B, 2015, 91, .	1.1	26
48	Valley blockade and multielectron spin-valley Kondo effect in silicon. Physical Review B, 2015, 92, .	1.1	15
49	Analysis of hyperfine structure in chalcogen-doped silicon and germanium nanowires. Physical Review B, 2015, 91, .	1.1	1
50	Ground and excited states of iron centers in ZnO: Pulse-EPR and magneto-optical spectroscopy. Physical Review B, 2015, 92, .	1.1	6
51	MOCVD growth and thermal analysis of Sb<inf>2</inf>Te<inf>3</inf> thin films and nanowires. , 2015, , .		2
52	Gradual set dynamics in HfO₂-based memristor driven by sub-threshold voltage pulses. , 2015, , .		15
53	(Invited) Defects and Dopants in Silicon and Germanium Nanowires. ECS Transactions, 2015, 69, 69-79.	0.3	2
54	Atomicâ€Scale Magnetic Properties of Truly 3dâ€Diluted ZnO. Advanced Electronic Materials, 2015, 1, 1400039.	2.6	17

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55	Universal set of quantum gates for double-dot exchange-only spin qubits with intradot coupling. Journal of Physics A: Mathematical and Theoretical, 2015, 48, 065304.	0.7	25
56	Silicene field-effect transistors operating at room temperature. Nature Nanotechnology, 2015, 10, 227-231.	15.6	1,429
57	Effective Hamiltonian for two interacting double-dot exchange-only qubits and their controlled-NOT operations. Quantum Information Processing, 2015, 14, 47-65.	1.0	18
58	Synaptic potentiation and depression in Al:HfO2-based memristor. Microelectronic Engineering, 2015, 147, 41-44.	1.1	53
59	Nucleation and temperature-driven phase transitions of silicene superstructures on Ag(1â€‰1â€‰1). Journal of Physics Condensed Matter, 2015, 27, 255005.	0.7	23
60	Influence of doping elements on the formation rate of silicon nanowires by silver-assisted chemical etching. Surface and Coatings Technology, 2015, 280, 37-42.	2.2	18
61	Ultrafast Dynamics in Epitaxial Silicene on Ag(111). Springer Proceedings in Physics, 2015, , 329-332.	0.1	2
62	Ultrafast dynamics in epitaxial silicene on Ag(111). , 2014, , .		0
63	Interstitial Fe in MgO. Journal of Applied Physics, 2014, 115, 023508.	1.1	7
64	Engineering the electronic properties of silicene by tuning the composition of MoX ₂ and GaX (X = S,Se,Te) chalchogenide templates. 2D Materials, 2014, 1, 011010.	2.0	53
65	Effective Hamiltonian for the hybrid double quantum dot qubit. Quantum Information Processing, 2014, 13, 1155-1173.	1.0	35
66	Effect on Al:MO2/In0.53Ga0.47As interface (M=Hf, Zr) of trimethyl-aluminum pre-treatment during atomic layer deposition. Thin Solid Films, 2014, 563, 44-49.	0.8	0
67	Synthesis of multiferroic Er-Fe-O thin films by atomic layer and chemical vapor deposition. Journal of Applied Physics, 2014, 115, .	1.1	4
68	Twoâ€Đimensional Si Nanosheets with Local Hexagonal Structure on a MoS₂ Surface. Advanced Materials, 2014, 26, 2096-2101.	11.1	311
69	Electrically detected magnetic resonance study of the Ge dangling bonds at the Ge(111)/GeO2 interface after capping with Al2O3 layer. Applied Surface Science, 2014, 291, 3-5.	3.1	0
70	Phase Stabilization of Al:HfO₂ Grown on In_xGa_{1â€“x}As Substrates (x = 0, 0.15, 0.53) via Trimethylaluminum-Based Atomic Layer Deposition. ACS Applied Materials & Interfaces, 2014, 6, 3455-3461.	4.0	25
71	Fe_{3â^’Î´}O₄/MgO/Co magnetic tunnel junctions synthesized by fullin situatomic layer and chemical vapour deposition. Journal Physics D: Applied Physics, 2014, 47, 102002.	1.3	16
72	Spin-dependent recombination and single charge dynamics in silicon nanostructrures. European Physical Journal Plus, 2014, 129, 1.	1.2	1

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73	Exploring the morphological and electronic properties of silicene superstructures. Applied Surface Science, 2014, 291, 109-112.	3.1	34
74	Vibrational properties of epitaxial silicene layers on (111) Ag. Applied Surface Science, 2014, 291, 113-117.	3.1	49
75	Theoretical aspects of graphene-like group IV semiconductors. Applied Surface Science, 2014, 291, 98-103.	3.1	23
76	Electron spin resonance of substitutional nitrogen in silicon. Physical Review B, 2014, 89, .	1.1	6
77	ToFâ€SIMS study of phosphorus diffusion in lowâ€dimensional silicon structures. Surface and Interface Analysis, 2013, 45, 386-389.	0.8	12
78	Thermal stability of highâ€Î° oxides on SiO₂/Si or Si_xN_y/SiO₂/Si for chargeâ€trapping nonvolatile memories. Surface and Interface Analysis, 2013, 45, 390-393.	0.8	19
79	Getting through the Nature of Silicene: An sp²â€“sp³ Two-Dimensional Silicon Nanosheet. Journal of Physical Chemistry C, 2013, 117, 16719-16724.	1.5	163
80	Evidence for graphite-like hexagonal AlN nanosheets epitaxially grown on single crystal Ag(111). Applied Physics Letters, 2013, 103, .	1.5	251
81	Low-temperature atomic layer deposition of MgO thin films on Si. Journal Physics D: Applied Physics, 2013, 46, 485304.	1.3	33
82	Hindering the Oxidation of Silicene with Nonâ€Reactive Encapsulation. Advanced Functional Materials, 2013, 23, 4340-4344.	7.8	161
83	Donor Wave Functions Delocalization in Silicon Nanowires: The Peculiar [011] Orientation. Nano Letters, 2013, 13, 4963-4968.	4.5	5
84	A Viable Route to Enhance Permittivity of Gate Dielectrics on In_{0.53}Ga_{0.47}As(001): Trimethylaluminum-Based Atomic Layer Deposition of MeO₂(Me = Zr, Hf). ECS Journal of Solid State Science and Technology, 2013, 2, P395-P399.	0.9	2
85	Trimethylaluminum-based Atomic Layer Deposition of MO2 (M=Zr, Hf): Gate Dielectrics on In0.53Ga0.47As(001) Substrates. ECS Transactions, 2013, 50, 11-19.	0.3	1
86	Evidence of Trigonal Dangling Bonds at the Ge(111)/Oxide Interface by Electrically Detected Magnetic Resonance. Physical Review Letters, 2013, 110, 206101.	2.9	15
87	(Invited) Structural and Chemical Stabilization of the Epitaxial Silicene. ECS Transactions, 2013, 58, 217-227.	0.3	5
88	Atomic Layer Deposition of Al-Doped ZrO2Thin Films as Gate Dielectric for In0.53Ga0.47As. Journal of the Electrochemical Society, 2012, 159, H220-H224.	1.3	11
89	Role of the Oxygen Content in the GeO2Passivation of Ge Substrates as a Function of the Oxidizer. Journal of the Electrochemical Society, 2012, 159, H555-H559.	1.3	2
90	Few electron limit of n-type metal oxide semiconductor single electron transistors. Nanotechnology, 2012, 23, 215204.	1.3	44

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91	Charge dynamics of a single donor coupled to a few-electron quantum dot in silicon. Applied Physics Letters, 2012, 100, .	1.5	25
92	Structural and electrical properties of atomic layer deposited Al-doped ZrO2 films and of the interface with TaN electrode. Journal of Applied Physics, 2012, 112, .	1.1	22
93	Electronic Properties of Pristine and Se Doped [001] Silicon Nanowires: An Ab Initio Study. Journal of Nanoscience and Nanotechnology, 2012, 12, 8704-8709.	0.9	5
94	Effect of Electric Dipoles on Fermi Level Positioning at the Interface between Ultrathin Al₂O₃ Films and Differently Reconstructed In_{0.53}Ga_{0.47}As(001) Surfaces. Journal of Physical Chemistry C, 2012, 116, 18746-18751.	1.5	4
95	The effect of a ferromagnetic Gd marker on the effective work function of Fe in contact with Al2O3/Si. Journal of Applied Physics, 2012, 111, 07C506.	1.1	5
96	Atomic layer deposition of rare-earth-based binary and ternary oxides for microelectronic applications. Semiconductor Science and Technology, 2012, 27, 074013.	1.0	38
97	Metal Organic Chemical Vapor Deposition of Phase Change Ge₁Sb₂Te₄ Nanowires. Nano Letters, 2012, 12, 1509-1515.	4.5	34
98	Fe charge state adjustment in ZnO upon ion implantation. Journal of Physics Condensed Matter, 2012, 24, 485801.	0.7	12
99	Geometrical Effects on Valley-Orbital Filling Patterns in Silicon Quantum Dots for Robust Qubit Implementation. Applied Physics Express, 2012, 5, 124001.	1.1	17
100	Local Electronic Properties of Corrugated Silicene Phases. Advanced Materials, 2012, 24, 5088-5093.	11.1	278
101	Synthesis of magnetic tunnel junctions with full in situ atomic layer and chemical vapor deposition processes. Thin Solid Films, 2012, 520, 4820-4822.	0.8	18
102	Chemical vapor deposition growth of Fe3O4 thin films and Fe/Fe3O4 bi-layers for their integration in magnetic tunnel junctions. Thin Solid Films, 2012, 520, 4617-4621.	0.8	22
103	Pulsed laser deposition of ultrathin BaTiO3/Fe bi-layers: Structural characterization and piezoelectric response. Thin Solid Films, 2012, 520, 4586-4589.	0.8	13
104	Atomic layer deposited TiO2 for implantable brain-chip interfacing devices. Thin Solid Films, 2012, 520, 4745-4748.	0.8	15
105	Reconstruction dependent reactivity of As-decapped In0.53Ga0.47As(001) surfaces and its influence on the electrical quality of the interface with Al2O3 grown by atomic layer deposition. Applied Physics Letters, 2011, 99, .	1.5	11
106	Synthesis and characterization of DyScO films deposited on Si and Si-rich SiN by atomic layer deposition for blocking layer replacement in TANOS stack. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 01AE03.	0.6	6
107	Ab initiostudy of magnetic properties of complexes formed by an Fe impurity and an intrinsic interstitial defect in ZnO. Physical Review B, 2011, 84, .	1.1	11
108	Fe/BaTiO3 interface: Band alignment and chemical properties. Applied Physics Letters, 2011, 99, 182905.	1.5	31

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109	Developmental factor IRF6 exhibits tumor suppressor activity in squamous cell carcinomas. Proceedings of the National Academy of Sciences of the United States of America, 2011, 108, 13710-13715.	3.3	141
110	Impact of post deposition annealing in the electrically active traps at the interface between Ge(001) substrates and LaGeOx films grown by molecular beam deposition. Journal of Applied Physics, 2011, 110, 084504.	1.1	8
111	Combining HRTEMâ€“EELS nano-analysis with capacitanceâ€“voltage measurements to evaluate high-Î² thin films deposited on Si and Ge as candidate for future gate dielectrics. Microelectronic Engineering, 2011, 88, 419-422.	1.1	6
112	Mass Production of Silicon MOS-SETs: Can We Live with Nano-Devicesâ€™ Variability?. Procedia Computer Science, 2011, 7, 266-268.	1.2	9
113	Confinement Effects and Hyperfine Structure in Se Doped Silicon Nanowires. Nano Letters, 2011, 11, 4509-4514.	4.5	7
114	EPR spectroscopy of weak exchange interactions between Co²⁺ ions in ZnO. Physica Status Solidi - Rapid Research Letters, 2011, 5, 138-140.	1.2	14
115	Effects of surface passivation during atomic layer deposition of Al2O3 on In0.53Ga0.47As substrates. Microelectronic Engineering, 2011, 88, 431-434.	1.1	16
116	Influence of the oxidation temperature on the non-trigonal Ge dangling bonds at the (100)Ge/GeO2 interface. Microelectronic Engineering, 2011, 88, 388-390.	1.1	4
117	Chemical nature of the passivation layer depending on the oxidizing agent in Gd2O3/GeO2/Ge stacks grown by molecular beam deposition. Microelectronic Engineering, 2011, 88, 403-406.	1.1	2
118	Structural and electrical properties of Er-doped HfO2 and of its interface with Ge (001). Microelectronic Engineering, 2011, 88, 415-418.	1.1	8
119	Al2O3 stacks on In0.53Ga0.47As substrates: In situ investigation of the interface. Microelectronic Engineering, 2011, 88, 435-439.	1.1	4
120	Magnetic resonance spectroscopy of defects at the dielectric-semiconductor interface: Ge substrates and Si nanowires (invited). Microelectronic Engineering, 2011, 88, 1482-1487.	1.1	8
121	Au-catalyzed self assembly of GeTe nanowires by MOCVD. Journal of Crystal Growth, 2011, 315, 152-156.	0.7	21
122	Control of filament size and reduction of reset current below 10Î¼A in NiO resistance switching memories. Solid-State Electronics, 2011, 58, 42-47.	0.8	103
123	Resistive switching characteristics of NiO films deposited on top of W or Cu pillar bottom electrodes. Thin Solid Films, 2011, 519, 3798-3803.	0.8	10
124	Electrically Detected Magnetic Resonance of Donors and Interfacial Defects in Silicon Nanowires. Nanoscience and Nanotechnology Letters, 2011, 3, 568-574.	0.4	7
125	The fabrication of tunable nanoporous oxide surfaces by block copolymer lithography and atomic layer deposition. Nanotechnology, 2011, 22, 335303.	1.3	23
126	Switching quantum transport in a three donors silicon fin-field effect transistor. Applied Physics Letters, 2011, 99, .	1.5	18

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127	Influence of lattice parameters on the dielectric constant of tetragonal ZrO2 and La-doped ZrO2 crystals in thin films deposited by atomic layer deposition on Ge(001). Applied Physics Letters, 2011, 99, 232907.	1.5	10
128	Pulse electron spin resonance investigation of bismuth-doped silicon: Relaxation and electron spin echo envelope modulation. Physical Review B, 2011, 83, .	1.1	13
129	Evaluation of DyScOx as an alternative blocking dielectric in TANOS memories with Si3N4 or Si-rich SiN charge trapping layers. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, .	0.6	6
130	Scaling analysis of submicrometer nickel-oxide-based resistive switching memory devices. Journal of Applied Physics, 2011, 109, .	1.1	70
131	Improved Performance of In$_{0.53}$Ga$_{0.47}$As-Based Metalâ€“Oxideâ€“Semiconductor Capacitors with Al:ZrO$_{2}$ Gate Dielectric Grown by Atomic Layer Deposition. Applied Physics Express, 2011, 4, 094103.	1.1	5
132	(Invited) Active Trap Determination at the Interface of Ge and In0.53Ga0.47 as Substrates with Dielectric Layers. ECS Transactions, 2011, 41, 203-221.	0.3	3
133	Direct Observation at Nanoscale of Resistance Switching in NiO Layers by Conductive-Atomic Force Microscopy. Applied Physics Express, 2011, 4, 051101.	1.1	15
134	Detection of the Tetragonal Phase in Atomic Layer Deposited La-Doped ZrO2 Thin Films on Germanium. Journal of the Electrochemical Society, 2011, 158, G194.	1.3	7
135	Atomic Layer Deposition of Al-Doped ZrO2 Thin Films for Advanced Gate Stack on III-V Substrates. ECS Transactions, 2011, 35, 431-440.	0.3	1
136	Adiabatic charge control in a single donor atom transistor. Applied Physics Letters, 2011, 98, 053109.	1.5	30
137	Detection of the Tetragonal and Monoclinic Phases and their Role on the Dielectric Constant of Atomic Layer Deposited La-Doped ZrO2 Thin Films on Ge (001). ECS Transactions, 2011, 35, 481-490.	0.3	1
138	Microwave Effects in Silicon Low Dimensional Nanostructures. Journal of Nanoscience and Nanotechnology, 2010, 10, 2650-2655.	0.9	0
139	Magnetism in iron implanted oxides: a status report. Hyperfine Interactions, 2010, 197, 43-52.	0.2	7
140	Observation of spin-lattice relaxations of dilute Fe3+ in MgO by MÃ¶ssbauer spectroscopy. Hyperfine Interactions, 2010, 197, 89-94.	0.2	17
141	MÃ¶ssbauer study of 57Fe in GaAs and GaP following 57Mn+ implantation. Hyperfine Interactions, 2010, 198, 15-22.	0.2	3
142	Rare earth-based high-k materials for non-volatile memory applications. Microelectronic Engineering, 2010, 87, 290-293.	1.1	9
143	High permittivity materials for oxide gate stack in Ge-based metal oxide semiconductor capacitors. Thin Solid Films, 2010, 518, S96-S103.	0.8	15
144	Interface analysis of Ge ultra thin layers intercalated between GaAs substrates and oxide stacks. Thin Solid Films, 2010, 518, S123-S127.	0.8	6

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145	Photoâ€EPR and magnetoâ€optical spectroscopy of iron centres in ZnO. Physica Status Solidi (B): Basic Research, 2010, 247, 1517-1520.	0.7	8
146	Ultraviolet optical near-fields of microspheres imprinted in phase change films. Applied Physics Letters, 2010, 96, 193108.	1.5	19
147	O3-based atomic layer deposition of hexagonal La2O3 films on Si(100) and Ge(100) substrates. Journal of Applied Physics, 2010, 108, 084108.	1.1	30
148	Dielectric properties of Erâ¯doped HfO2â€ˆ(Erâ¼15%) grown by atomic layer deposition for high-Îº gate stacks. Applied Physics Letters, 2010, 96, .	1.5	37
149	Measuring the temperature of a mesoscopic electron system by means of single electron statistics. Applied Physics Letters, 2010, 96, 113109.	1.5	12
150	Stark effect of confined shallow levels in phosphorus-doped silicon nanocrystals. Physical Review B, 2010, 81, .	1.1	8
151	Evaluation of HfLaOx as Blocking Layer for Innovative Nonvolatile Memory Applications. ECS Transactions, 2010, 33, 417-424.	0.3	2
152	Si nanocrystal synthesis in HfO₂/SiO/HfO₂multilayer structures. Nanotechnology, 2010, 21, 055606.	1.3	15
153	Paramagnetism in Mn/Fe implanted ZnO. Applied Physics Letters, 2010, 97, .	1.5	45
154	Phosphorus doping of ultra-small silicon nanocrystals. Nanotechnology, 2010, 21, 025602.	1.3	68
155	CVD synthesis of polycrystalline magnetite thin films: structural, magnetic and magnetotransport properties. Journal Physics D: Applied Physics, 2010, 43, 065002.	1.3	33
156	Influence of the oxidizing species on the Ge dangling bonds at the (100)Ge/GeO2 interface. Applied Physics Letters, 2010, 96, .	1.5	31
157	Sub-10 µA reset in NiO-based resistive switching memory (RRAM) cells. , 2010, , .		7
158	MÃ¶ssbauer study of 57Fe in GaAs and GaP following 57Mn+ implantation. , 2010, , 361-368.		0
159	Magnetism in iron implanted oxides: a status report. , 2010, , 43-52.		0
160	Observation of spin-lattice relaxations of dilute Fe3+ in MgO by MÃ¶ssbauer spectroscopy. , 2010, , 89-94.		0
161	Atomic layer deposition of LaxZr1â¯xO2â¯Îˆâ€ˆ(x=0.25) high-k dielectrics for advanced gate stacks. Applied Physics Letters, 2009, 94, .	1.5	37
162	Investigation of interfacial layer development between thin Al2O3 films grown using atomic layer deposition and Si(100), Ge(100), or GaAs(100). Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2009, 27, 443-448.	0.9	15

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163	Chemical and structural properties of atomic layer deposited La2O3 films capped with a thin Al2O3 layer. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2009, 27, L1-L7.	0.9	10
164	Interface quality of atomic layer deposited La-doped ZrO2 films on Ge-passivated In0.15Ga0.85As substrates. Materials Research Society Symposia Proceedings, 2009, 1194, 80.	0.1	0
165	Nuclear HBx binds the HBV minichromosome and modifies the epigenetic regulation of cccDNA function. Proceedings of the National Academy of Sciences of the United States of America, 2009, 106, 19975-19979.	3.3	403
166	Ge-based interface passivation for atomic layer deposited La-doped ZrO2 on III-V compound (GaAs,In0.15Ga0.85As) substrates. Applied Physics Letters, 2009, 95, 023507.	1.5	25
167	Compact silicon double and triple dots realized with only two gates. Applied Physics Letters, 2009, 95, .	1.5	38
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